Product data sheet

1. General description

PNP low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low R_{CEsat}
- High collector current capability
- High collector current gain
- · Improved efficiency due to reduced heat generation

3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-2	Α
I _{CRM}		$\delta \leq 0.25$; Operated under pulsed conditions; $t_p \leq 100$ ms	-	-	-3	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	135	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		C
3	С	collector		В—
			1 2	E sym132
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBSS5350T		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T	ZD%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.25$; Operated under pulsed conditions; $t_p \le 100 \text{ ms}$		-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	Α
I _B	base current			-	-0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- 4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width tp \leq 100 ms, duty cycle $\delta \leq$ 0.25.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	[2 [3 [4	[1]	-	-	417	K/W
			[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			[4]	-	-	250	K/W
			[1] [5]	-	-	104	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$

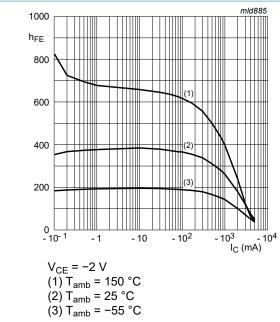
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = -100 \ \mu\text{A}; \ I_C = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	-6	-	-	V
СВО	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
1 _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	130	-	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; T _{amb} = 25 °C	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-	-90	mV
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-180	mV
		I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-320	mV
		I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-270	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-390	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	135	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.2	٧
T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	35	pF

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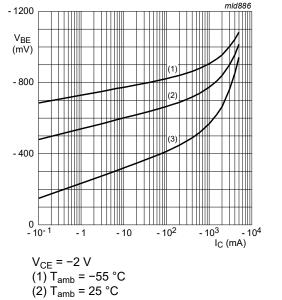


$$V_{CE} = -2 V$$

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values

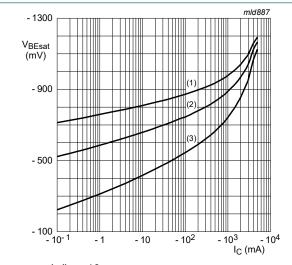


(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 2. Base-emitter voltage as a function of collector current; typical values



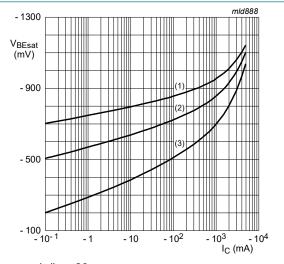
$$I_{\rm C}/I_{\rm B}=10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 3. Base-emitter saturation voltage as a function of Fig. 4. collector current; typical values



$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Base-emitter saturation voltage as a function of collector current; typical values

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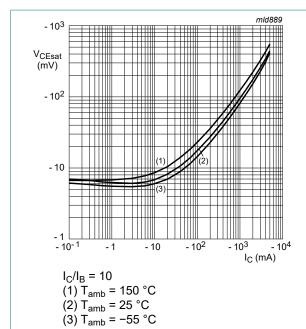


Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

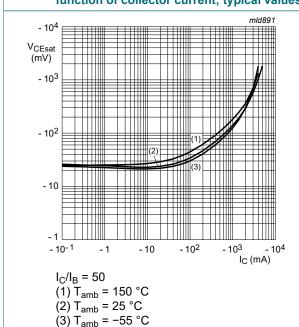
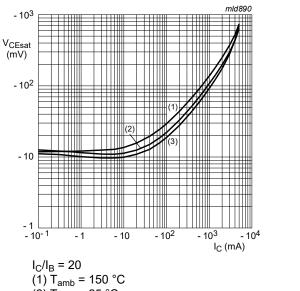
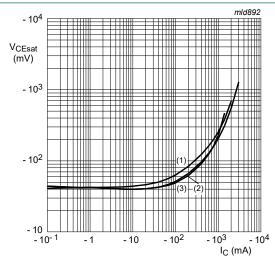


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



(1) T_{amb} = 150 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

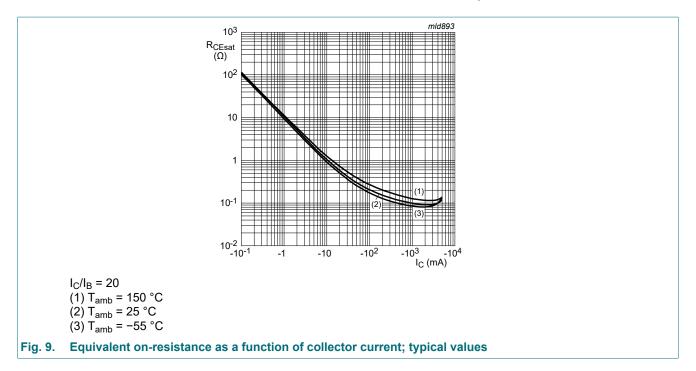
Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



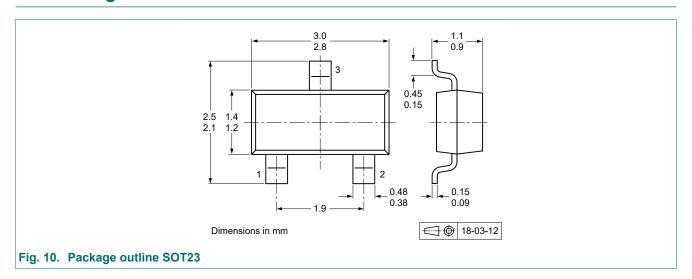
 $I_C/I_B = 100$ (1) $T_{amb} = 150 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -55 \,^{\circ}C$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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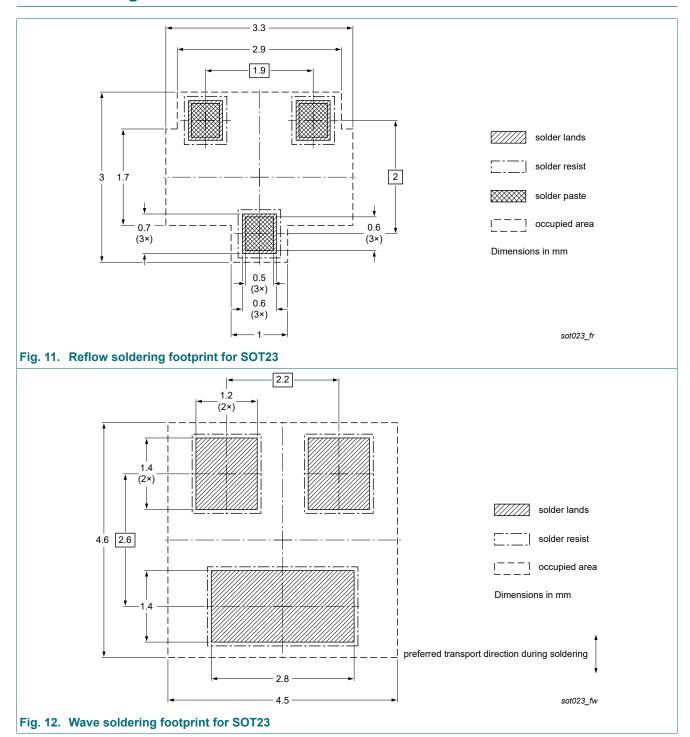


11. Package outline



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12. Soldering



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13. Revision history

Table 8. Revision history

Table 6. Nevision inistory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5350T v.4	20230101	Product data sheet	-	PBSS5350T v.3				
Modifications:		Product changed to non-automotive qualification. Please refer to nexperia.com for automotive(-Q) product alternative(s).						
PBSS5350T v.3	20220510	Product data sheet	-	PBSS5350T v.2				
PBSS5350T v.2	20040113	Product data sheet	-	PBSS5350T v.1				
PBSS5350T v.1	20020808	Product data sheet	-	-				

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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